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SHEET 1 OF 1 FORM PTO:1449 U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. APPLICATION NO. PATENT AND TRADEMARK OFFICE MICRON.154A 09/939,417 INFORMATION DISCLOSURE STATEMENT BY APPLICANT **APPLICANT** Forbes (LISE SEVERAL SHEETS IF NECESSARY) FILING DATE **GROUP** August 24, 2001 Unknown

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I ULU	21		U.S. PATENT DOCUMENTS			
EXAMPLER TRADE	MA OCUMENT NUMBER	DATE	NAME.	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
KI	5,909,618	06/01/99	Forbes et al.			
KP	5,936,274	08/10/99	Forbes et al.			
KP	5,973,356	10/26/99	Noble et al.			
RP	5,991,225	11/23/99	Forbes et al.		·	
KP	6,072,209	06/06/00	Noble et al.			
HP	6,124,729	*09/26/00	Noble et al.			
KP	6,134,175	10/17/00	Forbes et al.			
AP	6,143,636	11/07/00	Forbes et al.			
KP	6,150,687	11/21/00	Noble et al.			
KP	6,153,468	11/28/00	Forbes et al.			
KP	6,208,164	03/27/01	Noble et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER		DOCUMENT NUMBER	ДАТЕ	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
INITIAL			_				YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)				
	1.	Hergenrother et al., "The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET with Lithography-Independent Gate Length", Bell Laboratories, Lucent Technologies, NJ, USA, pages 1-4.			
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EXAMINER DATE CONSIDERED O - Q - Q = 0

\*EXAMINER: INTIALIF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.